

# Phase Control Thyristors (Hockey PUK Version), 650 A



**B-PUK (TO-200AC)** 

PRIMARY CHARACTERISTICS						
I <sub>T(AV)</sub>	650 A					
V <sub>DRM</sub> /V <sub>RRM</sub>	400 V, 800 V, 1200 V, 1400 V, 1600 V					
$V_{TM}$	1.90 V					
I <sub>GT</sub>	100 mA					
T <sub>J</sub>	-40 °C to +125 °C					
Package	B-PUK (TO-200AC)					
Circuit configuration	Single SCR					

#### **FEATURES**

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case B-PUK (TO-200AC))



- High profile hockey PUK
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
1		650	A				
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C				
1		1230	Α				
IT(RMS)	T <sub>hs</sub>	25	°C				
	50 Hz	9000	- A				
I <sub>TSM</sub>	60 Hz	9420	A				
l <sup>2</sup> t	50 Hz	405	kA <sup>2</sup> s				
1-1	60 Hz	370	- KA-S				
V <sub>DRM</sub> /V <sub>RRM</sub>		400 to 1600	V				
t <sub>q</sub>	Typical	100	μs				
T <sub>J</sub>		-40 to +125	°C				

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE F	VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM mA					
	04	400	500						
	80	800	900						
VS-ST330CL	12	1200	1300	50					
	14	1400	1500						
	16	1600	1700						



PARAMETER	SYMBOL		TEST CON	IDITIONS	VALUES	UNITS
Maximum average on-state current	L	180° condu	180° conduction, half sine wave		650 (314)	Α
at heatsink temperature	I <sub>T(AV)</sub>	double side	(single side) co	oled	55 (75)	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink tempe	erature double side cooled	1230	
		t = 10 ms	No voltage		9000	
Maximum peak, one-cycle non-repetitive surge current		t = 8.3 ms	reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	9420	A kA <sup>2</sup> s
	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RBM</sub>		7570	
		t = 8.3 ms	reapplied		7920	
	l <sup>2</sup> t	t = 10 ms	No voltage reapplied		405	
Maximum I <sup>2</sup> t for fusing		t = 8.3 ms			370	
		t = 10 ms			287	
		t = 8.3 ms	reapplied		262	
Maximum I <sup>2</sup> √t for fusing	I²√t	t = 0.1 to 10	ms, no voltage	reapplied	4050	kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.91	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x π	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.57	11122
Maximum on-state voltage	$V_{TM}$	I <sub>pk</sub> = 1730 A	$I_{pk} = 1730 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			V
Maximum holding current	I <sub>H</sub>	T _ 05 °C	anada auppli: 1	2 V registive lead	600	mΛ
Typical latching current	ΙL	1 J = 25 °C,	anoue supply 1	2 V resistive load	1000	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/μs
Typical delay time	t <sub>d</sub>	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.0	-10
Typical turn-off time	tq	$I_{TM}$ = 550 A, $T_J$ = $T_J$ maximum, dl/dt = 40 A/μs, $V_R$ = 50 V, dV/dt = 20 V/μs, gate 0 V 100 $\Omega$ , $t_p$ = 500 μs	100	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$	500	V/µs
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	50	mA



TRIGGERING								
PARAMETER	SYMBOL	TEG	ST CONDITIONS	VALUES		UNITS		
PANAMETEN	STIVIBUL	IES	ST CONDITIONS	Тур.	Max.	UNITS		
Maximum peak gate power	$P_{GM}$	$T_J = T_J$ maximum,	t <sub>p</sub> ≤ 5 ms	10	W			
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	l vv		
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum,	t <sub>p</sub> ≤ 5 ms	3	.0	Α		
Maximum peak positive gate voltage	+V <sub>GM</sub>	T T manyimum	t c E ma	2	:0	V		
Maximum peak negative gate voltage	-V <sub>GM</sub>	ij = ij maximum,	$T_J = T_J$ maximum, $t_p \le 5$ ms					
		T <sub>J</sub> = -40 °C		200	-			
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	]	100	200	mA		
		T <sub>J</sub> = 125 °C	Maximum required gate trigger/ current/voltage are the lowest	50	-	1		
		T <sub>J</sub> = -40 °C	value which will trigger all units	2.5	-			
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.8	3.0	V		
		T <sub>J</sub> = 125 °C		1.1	-			
DC gate current not to trigger	I <sub>GD</sub>	T T	Maximum gate current/voltage not to trigger is the maximum	1	0	mA		
DC gate voltage not to trigger	$V_{\mathrm{GD}}$	$T_J = T_J$ maximum	value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.25		V		

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum operating junction temperature range	$T_{J}$		-40 to +125	°C			
Maximum storage temperature range	T <sub>Stg</sub>		-40 to +150	C			
Maximum thermal resistance, junction to heatsink	D	DC operation single side cooled	0.11				
waximum thermal resistance, junction to heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.06	K/W			
Maximum thermal resistance, case to heatsink	В	DC operation single side cooled	0.011	IV VV			
waximum thermal resistance, case to heatsink	R <sub>thC-hs</sub>	DC operation double side cooled	0.005				
Mounting force, ± 10 %			9800 (1000)	N (kg)			
Approximate weight			250	g			
Case style		See dimensions - link at the end of datasheet	B-PUK (TO-	200AC)			

△R <sub>thJ-hs</sub> CONDUCTION									
CONDUCTION ANGLE	SINUSOIDAL C		RECTANGULAR	RCONDUCTION	TEST CONDITIONS	UNITS			
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS			
180°	0.012	0.010	0.008	0.008					
120°	0.014	0.015	0.014	0.014					
90°	0.018	0.018	0.019	0.019	$T_J = T_J$ maximum	K/W			
60°	0.026	0.027	0.027	0.028					
30°	0.045	0.046	0.046	0.046					

#### Note

• The table above shows the increment of thermal resistance R<sub>thJ-hs</sub> when devices operate at different conduction angles than DC



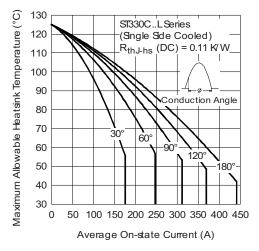


Fig. 1 - Current Ratings Characteristics

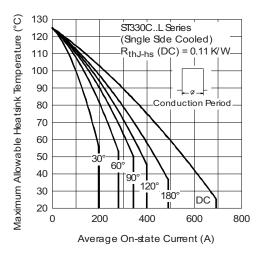


Fig. 2 - Current Ratings Characteristics

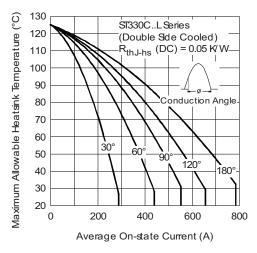


Fig. 3 - Current Ratings Characteristics

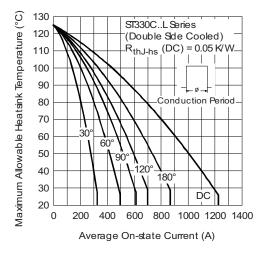


Fig. 4 - Current Ratings Characteristics

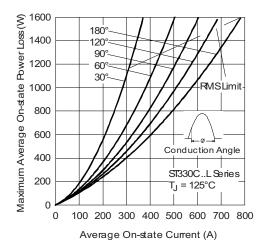


Fig. 5 - On-State Power Loss Characteristics

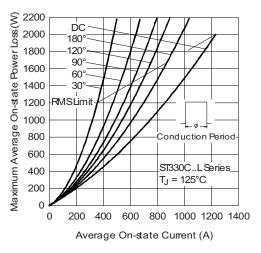


Fig. 6 - On-State Power Loss Characteristics

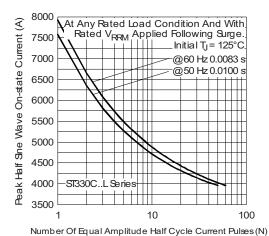


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

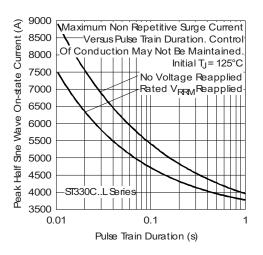


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

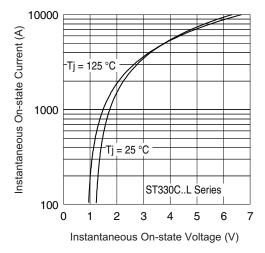


Fig. 9 - On-State Voltage Drop Characteristics

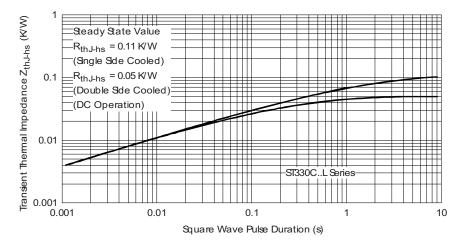


Fig. 10 - Thermal Impedance Z<sub>thJ-hs</sub> Characteristics

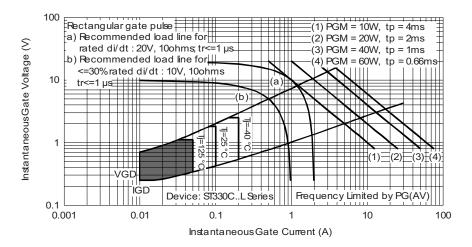


Fig. 11 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

Device code	VS-	ST	33	0	С	16	L	1	-	
	1	2	3	4	5	6	7	8	9	'
	1 -		nay Sen ristor	niconduc	ctors pro	oduct				
	3 -	_		art numb	oer					
	4 -	. 0 =	convert	er grade	)					
	5 -	. C=	cerami	: PUK						
	6 -	- Volt	age cod	de x 100	= V <sub>RRN</sub>	(see V	oltage F	Ratings	table)	
	7 -	. L=	PUK ca	se B-PL	JK (TO-	200AC)				
	8 -	. 0 =	eyelet t	erminals	gate a	and auxi	iliary ca	thode u	nsolder	ed leads)
		1 =	fast-on	terminal	s (gate	and aux	kiliary ca	athode (	unsolde	red leads)
		2 =	eyelet t	erminals	gate a	ınd auxi	iliary ca	thode s	oldered	leads)
		3 = 1	fast-on t	erminals	(gate ar	nd auxilia	ary cath	ode solo	lered lea	ds)
	9 -	- Crit	ical dV/	dt: • No	ne = 50	0 V/µs (	(standar	rd selec	tion)	

LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95076

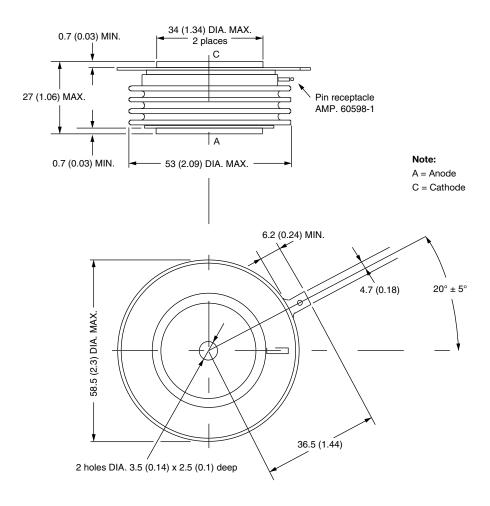
• L = 1000 V/µs (special selection)



# **B-PUK (TO-200AC)**

#### **DIMENSIONS** in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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